Journal of Material Sciences & Manufacturing Research



Research Article

Influence of Additive Nd₂O₃ on Dielectric Constants for Ternary Na₂B₄O₇-SiO₂-Ge₂O₃ System

Mundher M1*, Bendary AA1, Farag MA1, Abu Bakr El- Bediwi2 and Hassaan MY1

¹Physics Department, Faculty of Science, Al-Azhar University, Egypt

²Physics Department, Faculty of Science, Mansoura University, Mansoura, Egypt

ABSTRACT

The dielectric constant and the power factor can be varied by changes in the glass composition. The present work aims to understand the effect of Nd_2O_3 on dielectric properties of $Na_2B_4O_7$ - SiO_2 - Ge_2O_3 system. The results show that, $\ln \sigma$, exponent factor S, ε' and ε'' values of $Na_2B_4O_7$ - SiO_2 - Ge_2O_3 increased with increasing Nd_2O_3 content. ε' and ε'' values of $Na_2B_4O_7$ - SiO_2 - Ge_2O_3 increased with increasing temperature. Activation energy, the exponent factor S and M' values of $Na_2B_4O_7$ - SiO_2 - Ge_2O_3 decreased with increasing Nd_2O_3 content. ε for $Na_2B_4O_7$ - SiO_2 - Ge_2O_3 decreased with increasing temperature. M' value decreased with increasing temperature, but it increasing frequency.

*Corresponding authors

Abu Bakr El- Bediw, Physics Department, Faculty of Science, Mansoura University, Mansoura, Egypt.

Received: July 25, 2022; Accepted: August 01, 2023; Published: August 16, 2023

Keywords: $Na_2B_4O_7$ -SiO₂-Ge₂O₃ Ternary System, Dielectric Constants, Nd_2O_3

Introduction

Amorphous solids are compounds without long range order and periodicity, where glasses are a subset of its which show a distinct glass transition temperature made by solidifying molten silicon dioxide with other chemical compounds. Glasses established significant attention due to their sole properties such as hardness, excellent corrosion resistance, good strength and transparency. The structure of glass through many years studied by infrared spectroscopy, differential scanning calorimetry and x-ray diffraction analysis [1-4]. Transition metal oxides have various interesting properties as superconductivity, magneto resistance, fiber optic communication devices, piezoelectricity solid-state lasers luminescent and solar energy concentrators [5]. Some research for the SiO₂ -B₂O₃ -Na₂O ternary system have shown breaking down the original network, due to that alkali cations (Na⁺) can played as charge compensators in the four coordinated boron [6, 7]. The aim of this work is to study the effect of Nd_2O_3 on dielectric properties of Na₂B₄O₇-SiO₂-Ge₂O₃ system.

Experimental Details

Na₂B₄O₇-SiO₂-(Ge₂O₃)_{2.5-x}-(Nd₂O₃)_x (x=0, 1, 1.5 and 2.5 mol. %) samples, Table 1, were prepared by the conventional melt quench technique, with high purity (99.9%) components powders, obtained from Sigma Aldrich. A pure regent of the starting materials is mixed with the proper ratios. The mixture for each sample was well grinded to insure the homogeneity of the powder. The mixture powder was melted in porcelain crucible at 1200 °C for one hour. The molten mixture was stirred gradually to ensure the homogeneity. The molten samples were poured and quenched between two brass plates. The produced samples were annealed for 2 hours to reduce thermal stresses inside the samples. The

dielectric measurements of used glasses were carried out by means of a Novocontrol high resolution alpha dielectric analyzer in the frequency range 0.01 Hz to 10 MHz. The analyzer was supported by Quatro temperature controller using pure nitrogen as heating agent and providing a temperature stability better than 0.2 K. The measurements were conducted using gold-plated stainlesssteel electrodes of 20 mm in diameter in parallel plate capacitor configuration.

Tal	ble	1:	Composition	of	Used	Samples	5
-----	-----	----	-------------	----	------	---------	---

Samples	$Na_2B_4O_7$	SiO ₂	Ge ₂ O ₃	Nd ₂ O ₃
G1	70	15	15	0
G6	70	15	14	1
G7	70	15	13.5	1.5
G8	70	15	13	2
G9	70	15	12.5	2.5

Results And Discussions Dielectric Constant

Figure 1 shows the relation between $\ln \sigma$ and activation energy versus Nd_2O_3 concentration for $Na_2B_4O_7$ - SiO_2 -(Ge_2O_3)_{2.5-x-}(Nd_2O_3)_x. It is obvious that, $\ln \sigma$ value increased but of the dc conductivity activation energy deceased with increasing Nd_2O_3 content. Also Figure 2 shows the relation between $\ln \sigma$ and 1000/T for $Na_2B_4O_7$ - SiO_2 -(Ge_2O_3)_{2.5-x-}(Nd_2O_3)_x at different frequencies. The results show $\ln \sigma$ increased with increasing frequency and temperature. hat is may be attributed to the partial conversion of BO_4 to BO_3 structural units with the formation of non-bridging oxygen atoms, because the electrons are less tightly bound to the nuclear charge and easily excite from the valence to conduction band. Moreover, the presence of Nd ions affects the network structure increasing the number of free electrons leading to increase conductivity.

Citation: Mundher M, Bendary AA, Farag MA, Abu Bakr El- Bediwi, Hassaan MY (2023) Influence of Additive Nd₂O₃ on Dielectric Constants for Ternary Na₂B₄O₇-SiO₂-Ge₂O₃ System. Journal of Material Sciences & Manufacturing Research. SRC/JMSMR-179. DOI: doi.org/10.47363/JMSMR/2023(4)156



Figure 1: $\ln \sigma$ and Activation Energy Versus Nd₂O₃ Concentration for Na₂B₄O₇-SiO₂-(Ge₂O₃)2.5-x-(Nd₂O₃)x



Figure 2: $\ln \sigma$ versus 1000/T for Na₂B₄O₇-SiO₂-(Ge₂O₃)2.5-x-(Nd₂O₃)x at Different Frequency

The frequency dependence of the total conductivity $\sigma(\omega)$ of all amorphous materials and glasses follows relation: $\sigma(\omega) = \sigma_{d_c}(0) + A \omega^s$

Where $\sigma_{dc}(0)$ is the frequency independent conductivity, A is a constant, S is the exponent factor and ω is the angular frequency. The dielectric loss factor describes the loss of electric field energy in the material. Therefore, the exponent s was obtained by plot log σ_{total} versus log ω . The relation between the exponent factor S and T for Na₂B₄O₇-SiO₂-(Ge₂O₃)2.5-x-(Nd₂O₃)x, Figure 3, shows it decreased with increasing temperature and increased with increasing Nd₂O₃ content.

Citation: Mundher M, Bendary AA, Farag MA, Abu Bakr El- Bediwi, Hassaan MY (2023) Influence of Additive Nd, O, on Dielectric Constants for Ternary Na, B, O,-SiO₂-Ge₂O₂ System. Journal of Material Sciences & Manufacturing Research. SRC/JMSMR-179. DOI: doi.org/10.47363/JMSMR/2023(4)156



Figure 3: Exponent Factor S, versus T for Na₂B₄O₇-SiO₂-(Ge₂O₃)2.5-x-(Nd₂O₃)x

The dielectric constant was measured in the frequency range 0.01 Hz up to 10 MHz. The value of dielectric loss (ε) for Na,B₄O₂-SiO₂-Ge₂O₃ increased after Nd₂O₃ adding content as shown in Figure 4. The relation between dielectric constant (ε') and temperature for $Na_{A}B_{A}O_{7}$ -SiO₂-(Ge₂O₃)_{2.5-x-}(Nd₂O₃)_x, Figure 5, shows ε' increased with increasing at low frequency with a slight or no change at high frequency. The value of the dielectric loss factor (ε ") increased with increasing Nd₂O₂ concentration in Na₂B₂O₂-SiO₂- $(Ge_2O_3)_{2.5-x-}(Nd_2O_3)_x$ as shown in Figure 6. The relation between ε'' and temperature for $Na_2B_2O_2-SiO_2-(Ge_2O_3)_{2.5-x-}(Nd_2O_3)_x$ shown in Figure 7, shows E" increased with increasing temperature at low frequency but increased slowly with increasing temperature at high frequency. That is meant, the variation of the dielectric constant is large at low frequency and vice versa, which can be attributed to the orientational polarization is related to the thermal motion of molecules [8] and/or the space charge polarization due to the bonding defects in the structure [9]. The dielectric constant decrease with increasing frequency is a normal dielectric behavior where that agreed by other researchers [10-12].



Figure 4: ε' Versus Nd₂O₂ Concentration

Citation: Mundher M, Bendary AA, Farag MA, Abu Bakr El- Bediwi, Hassaan MY (2023) Influence of Additive Nd₂O₃ on Dielectric Constants for Ternary Na₂B₄O₇-SiO₂-Ge₂O₃ System. Journal of Material Sciences & Manufacturing Research. SRC/JMSMR-179. DOI: doi.org/10.47363/JMSMR/2023(4)156



Figure 5: ε' Versus Temperature for Na₂B₄O₇-SiO₂-(Ge₂O₃)2.5-x-(Nd₂O₃)x at Different Frequency



Figure 6: ε" versus Nd₂O₃ Concentration



Figure 7: ε'' Versus Temperature for Na₂B₄O₇-SiO₂-(Ge₂O3)2.5-x-(Nd₂O₃)x

Citation: Mundher M, Bendary AA, Farag MA, Abu Bakr El- Bediwi, Hassaan MY (2023) Influence of Additive Nd₂O₃ on Dielectric Constants for Ternary Na₂B₄O₇-SiO₂-Ge₂O₃ System. Journal of Material Sciences & Manufacturing Research. SRC/JMSMR-179. DOI: doi.org/10.47363/JMSMR/2023(4)156

The M' value decreased with increasing Nd₂O₃ concentration in Na₂B₄O₇-SiO₂-(Ge₂O₃)2.5-x-(Nd₂O₃)x as shown in shown Figure 8. Also, the relation of M' versus temperature for Na₂B₄O₇-SiO₂-(Ge₂O₃)2.5-x-(Nd₂O₃)x shows, it decreased with increasing temperature, but it increased with increasing frequency.



Figure 8: M' Versus Temperature for $Na_2B_4O_7$ -SiO₂-(Ge₂O₃)2.5-x-(Nd₂O₃)x

Conclusion

Our 11B NMR spectra results show that, adding Nd₂O₃ to Na₂B₄O₇-SiO₂-Ge₂O₃ decreased the degree of connectivity and breaking of Si-O-Si bond, and formed anti-symmetric stretching of Si-O-Nd, therefore, Nd₂O₃ enter network as a modifier and affected the probability of N₄ formation causing a change in dielectric constants.

References

- Pan A, Ghosh AJ (2000) A new family of lead-bismuthate glass with a large transmitting window. Non-Cryst Solids 271: 157-161.
- Jiri Šubcik, Ladislav Koudelka, Petr Mosner, Lionel Montagne, Bertrand Revel, et al. (2009) non-Cryst. Solids 355: 970-975.
- 3. Adrian CW (2010) Physics and Chemistry of Glasses-European. Journal of Glass Science and Technology Part B 51: 1-39.
- Pal M (1996) Structure and physical properties of sodium antimony germanate glasses. Journal of Materials Research 11: 1831-1835.
- 5. Kreidl NJ (1990) Recent applications of glass science. Non-Cryst. Solids 123: 377-384.
- 6. Aboutaleb D, Douglad J, Safi B, Jbara O, Iratni A (2012) Phase Separation and Chemical Durability in the SiO₂-B₂O₃-

Na₂O (SBN) Glass System. Asian Journal of Chemistry 24: 473-480.

- 7. Dietzel R (1948) Glass structure and glass properties. Glasstech Ber 22: 81-86.
- 8. Brus LE (1984) Electron–electron and electron-hole interactions in small semiconductor crystallites: The size dependence of the lowest excited electronic state. J Chem Phys 80: 4403-4409.
- 9. Kayanuma Y (1986) Wannier exciton in microcrystals. Solid State Communications 59: 405-408.
- Mahmoudi CH, Hassanzadeh A, Golzan MM, Sedghi H, Talebian M (2011) Frequency dependence of ultrahigh dielectric constant of novel synthesized SnO2 nanoparticles thick films. Current Applied Physics 11: 409-413.
- 11. Venkataraman BH, Varma KBR (2004) Frequency-dependent dielectric characteristics of ferroelectric SrBi2Nb2O9 ceramics. Solid State Ionics 167: 197-202.

Copyright: ©2023 Abu Bakr El- Bediw, et al. This is an open-access article distributed under the terms of the Creative Commons Attribution License, which permits unrestricted use, distribution, and reproduction in any medium, provided the original author and source are credited.